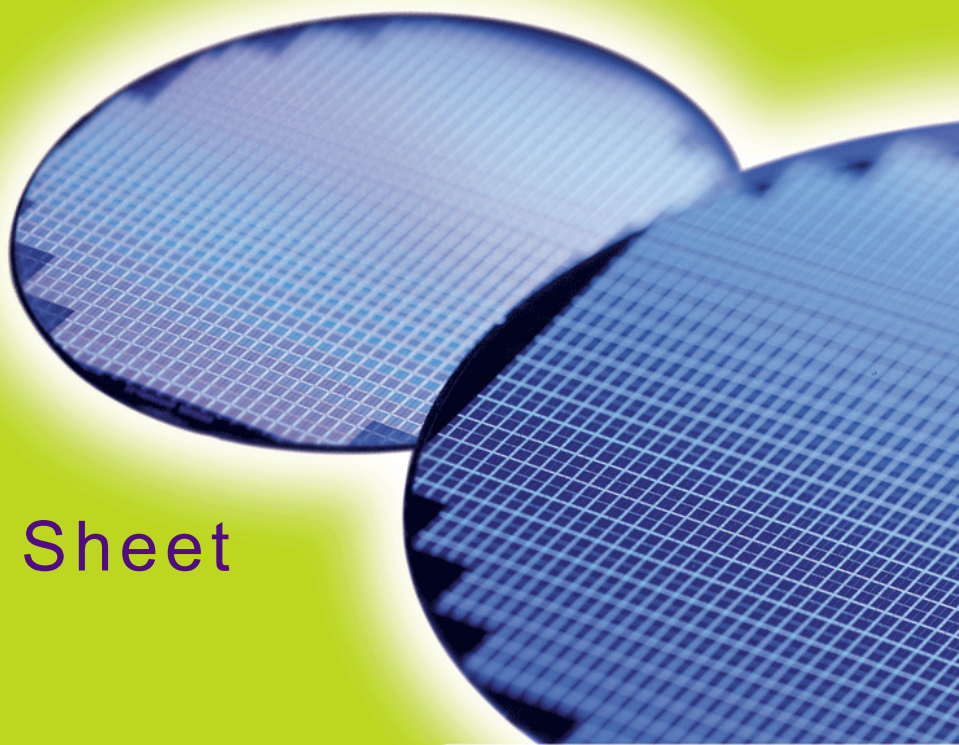


# **HYB18T512161CF-[16/20]**

*512-Mbit x16 DDR2 SDRAM  
DDR2 SDRAM  
EU RoHS compliant*



## **Internet Data Sheet**

*Rev. 1.11*



HYB18T512161CF  
512-Mbit Double-Data-Rate-Two SDRAM

<b>HYB18T512161CF-[16/20]</b>	
<b>Revision History: 2008-08, Rev. 1.11</b>	
<b>Page</b>	<b>Subjects (major changes since last revision)</b>
All	Removed 400 MHz
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All	Adapted Internet Edition

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# 1 Overview

This chapter gives an overview of the 512-Mbit Double-Data-Rate-Two SDRAM product family for graphics applications and describes its main characteristics.

## 1.1 Features

The 512-Mbit Double-Data-Rate-Two SDRAM offers the following key features:

- $1.8\text{ V} \pm 0.1\text{ V } V_{DD}$  for [-16/-20]
- $1.8\text{ V} \pm 0.1\text{ V } V_{DDQ}$  for [-16/-20]
- DRAM organizations with 16 data in/outputs
- Double Data Rate architecture:
  - two data transfers per clock cycle
  - four internal banks for concurrent operation
- Programmable  $\overline{\text{CAS}}$  Latency: 3, 4, 5, 6, 7
- Programmable Burst Length: 4 and 8
- Differential clock inputs (CK and  $\overline{\text{CK}}$ )
- Bi-directional, differential data strobes (DQS and  $\overline{\text{DQS}}$ ) are transmitted / received with data. Edge aligned with read data and center-aligned with write data.
- DLL aligns DQ and DQS transitions with clock
- $\overline{\text{DQS}}$  can be disabled for single-ended data strobe operation
- Commands entered on each positive clock edge, data and data mask are referenced to both edges of DQS
- Data masks (DM) for write data
- Posted  $\overline{\text{CAS}}$  by programmable additive latency (0-6) for better command and data bus efficiency
- Off-Chip-Driver impedance adjustment (OCD) and On-Die-Termination (ODT) for better signal quality.
- Auto-Precharge operation for read and write bursts
- Auto-Refresh, Self-Refresh and power saving Power-Down modes
- Average Refresh Period  $7.8\text{ }\mu\text{s}$  at a  $T_{\text{CASE}}$  lower than  $85^{\circ}\text{C}$ ,  $3.9\text{ }\mu\text{s}$  between  $85^{\circ}\text{C}$  and  $95^{\circ}\text{C}$
- Full Strength and reduced Strength (60%) Data-Output Drivers
- 2 K page size
- Package: P-TFBGA-84
- RoHS Compliant Products<sup>1)</sup>



**TABLE 1**  
Ordering Information for RoHS compliant products

Product Number	Org.	Clock (MHz)	Package
HYB18T512161CF-[-16/20]	× 16	600/500	P-TFBGA-84

1) RoHS Compliant Product: Restriction of the use of certain hazardous substances (RoHS) in electrical and electronic equipment as defined in the directive 2002/95/EC issued by the European Parliament and of the Council of 27 January 2003. These substances include mercury, lead, cadmium, hexavalent chromium, polybrominated biphenyls and polybrominated biphenyl ethers.

HYB18T512161CF  
512-Mbit Double-Data-Rate-Two SDRAM

## 1.2 Description

The 512-Mbit DDR2 SDRAM is a high-speed Double-Data-Rate-Two CMOS Synchronous DRAM device containing 536, 870, 912 bits and internally configured as a quad bank DRAM. The 512-Mb device is organized as 8 Mbit  $\times$  16 I/O  $\times$  4 banks chip. These synchronous devices achieve high speed transfer rates starting at 800 Mb/sec/pin for general applications.

The device is designed to comply with all DDR2 DRAM key features:

1. posted  $\overline{\text{CAS}}$  with additive latency,
2. write latency = read latency - 1,
3. normal and weak strength data-output driver,
4. Off-Chip Driver (OCD) impedance adjustment
5. On-Die Termination (ODT) function.

All of the control and address inputs are synchronized with a pair of externally supplied differential clocks. Inputs are latched at the cross point of differential clocks (CK rising and  $\overline{\text{CK}}$  falling). All I/Os are synchronized with a single ended DQS or differential DQS- $\overline{\text{DQS}}$  pair in a source synchronous fashion.

A 15-bit address bus is used to convey row, column and bank address information in a  $\overline{\text{RAS}}$ - $\overline{\text{CAS}}$  multiplexing style.

An Auto-Refresh and Self-Refresh mode is provided along with various power-saving power-down modes.

The functionality described and the timing specifications included in this data sheet are for the DLL Enabled mode of operation.

The DDR2 SDRAM is available in P-TFBGA package.



## 2 Configuration

### 2.1 Chip Configuration

The chip configuration of a DDR2 SDRAM is listed by function in **Table 2**. The abbreviations used in the Ball# and Buffer Type columns are explained in **Table 3** and **Table 4** respectively. The ball numbering for the FBGA package is depicted in **Figure 1**.

**TABLE 2**  
Chip Configuration of DDR2 SDRAM

Ball#	Name	Ball Type	Buffer Type	Function
<b>Clock Signals</b>				
J8	CK	I	SSTL	<b>Clock Signal CK, Complementary Clock Signal <math>\overline{CK}</math></b> <i>Note: CK and <math>\overline{CK}</math> are differential system clock inputs. All address and control inputs are sampled on the crossing of the positive edge of CK and negative edge of <math>\overline{CK}</math>. Output (read) data is referenced to the crossing of CK and <math>\overline{CK}</math> (both direction of crossing)</i>
K8	$\overline{CK}$	I	SSTL	
K2	CKE	I	SSTL	<b>Clock Enable</b> <i>Note: CKE HIGH activates and CKE LOW deactivates internal clock signals and device input buffers and output drivers. Taking CKE LOW provides Precharge Power-Down and Self-Refresh operation (all banks idle), or Active Power-Down (row Active in any bank). CKE is synchronous for power down entry and exit and for self-refresh entry. Input buffers excluding CKE are disabled during self-refresh. CKE is used asynchronously to detect self-refresh exit condition. Self-refresh termination itself is synchronous. After <math>V_{REF}</math> has become stable during power-on and initialisation sequence, it must be maintained for proper operation of the CKE receiver. For proper self-refresh entry and exit, <math>V_{REF}</math> must be maintained to this input. CKE must be maintained HIGH throughout read and write accesses. Input buffers, excluding CK, <math>\overline{CK}</math>, ODT and CKE are disabled during power-down</i>
<b>Control Signals</b>				
K7	$\overline{RAS}$	I	SSTL	<b>Row Address Strobe (RAS), Column Address Strobe (CAS), Write Enable (WE)</b>
L7	$\overline{CAS}$	I	SSTL	
K3	$\overline{WE}$	I	SSTL	
L8	$\overline{CS}$	I	SSTL	<b>Chip Select</b>
<b>Address Signals</b>				
L2	BA0	I	SSTL	<b>Bank Address Bus 1:0</b>
L3	BA1	I	SSTL	



HYB18T512161CF  
512-Mbit Double-Data-Rate-Two SDRAM

Ball#	Name	Ball Type	Buffer Type	Function
M8	A0	I	SSTL	<b>Address Signal 12:0, Address Signal 10/Autoprecharge</b>
M3	A1	I	SSTL	
M7	A2	I	SSTL	
N2	A3	I	SSTL	
N8	A4	I	SSTL	
N3	A5	I	SSTL	
N7	A6	I	SSTL	
P2	A7	I	SSTL	
P8	A8	I	SSTL	
P3	A9	I	SSTL	
M2	A10	I	SSTL	
	AP	I	SSTL	
P7	A11	I	SSTL	
R2	A12	I	SSTL	
<b>Data Signals</b>				
G8	DQ0	I/O	SSTL	<b>Data Signal 15:0</b> <i>Note: Bi-directional data bus. DQ[15:0]</i>
G2	DQ1	I/O	SSTL	
H7	DQ2	I/O	SSTL	
H3	DQ3	I/O	SSTL	
H1	DQ4	I/O	SSTL	
H9	DQ5	I/O	SSTL	
F1	DQ6	I/O	SSTL	
F9	DQ7	I/O	SSTL	
C8	DQ8	I/O	SSTL	
C2	DQ9	I/O	SSTL	
D7	DQ10	I/O	SSTL	
D3	DQ11	I/O	SSTL	
D1	DQ12	I/O	SSTL	
D9	DQ13	I/O	SSTL	
B1	DQ14	I/O	SSTL	
B9	DQ15	I/O	SSTL	
<b>Data Strobe</b>				
B7	UDQS	I/O	SSTL	<b>Data Strobe Upper Byte</b> <i>Note: UDQS corresponds to the data on DQ[15:8]</i>
A8	$\overline{\text{UDQS}}$	I/O	SSTL	
F7	LDQS	I/O	SSTL	<b>Data Strobe Lower Byte</b> <i>Note: LDQS corresponds to the data on DQ[7:0]</i>
E8	$\overline{\text{LDQS}}$	I/O	SSTL	
<b>Data Mask</b>				
B3	UDM	I	SSTL	<b>Data Mask Upper/Lower Byte</b> <i>Note: LDM and UDM are the input mask signals and control the lower or upper bytes.</i>
F3	LDM	I	SSTL	
<b>Power Supplies</b>				



HYB18T512161CF  
512-Mbit Double-Data-Rate-Two SDRAM

Ball#	Name	Ball Type	Buffer Type	Function
A9,C1,C3,C7,C9	$V_{DDQ}$	PWR	–	I/O Driver Power Supply
A1	$V_{DD}$	PWR	–	Power Supply
A7,B2,B8,D2,D8	$V_{SSQ}$	PWR	–	I/O Driver Power Supply
A3,E3	$V_{SS}$	PWR	–	Power Supply
<b>Power Supplies</b>				
J2	$V_{REF}$	AI	–	I/O Reference Voltage
E9, G1, G3, G7, G9	$V_{DDQ}$	PWR	–	I/O Driver Power Supply
J1	$V_{DDL}$	PWR	–	Power Supply
E1, J9, M9, R1	$V_{DD}$	PWR	–	Power Supply
E7, F2, F8, H2, H8	$V_{SSQ}$	PWR	–	I/O Driver Power Supply
J7	$V_{SSDL}$	PWR	–	Power Supply
A3, E3,J3,N1,P9	$V_{SS}$	PWR	–	Power Supply
<b>Not Connected</b>				
A2, E2, R3, R7, R8, L1	NC	NC	–	Not Connected
<b>Other Balls</b>				
K9	ODT	I	SSTL	<b>On-Die Termination Control</b> <i>Note: ODT is applied to each DQ, UDQS, <math>\overline{UDQS}</math>, LDQS, <math>\overline{LDQS}</math>, UDM and LDM signal. An EMRS(1) control bit enables or disables the ODT functionality.</i>

**TABLE 3**  
Abbreviations for Ball Type

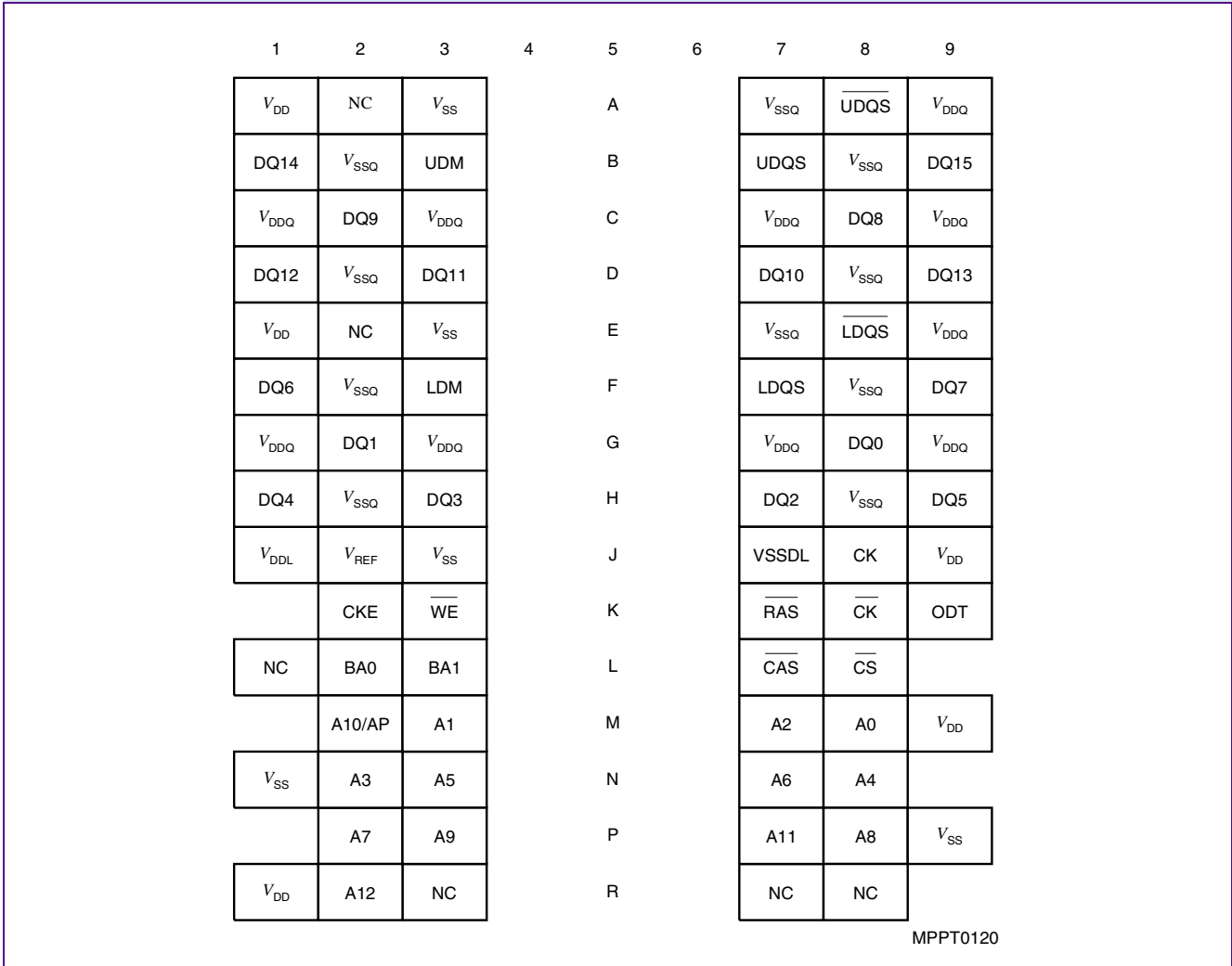
Abbreviation	Description
I	Standard input-only ball. Digital levels.
O	Output. Digital levels.
I/O	I/O is a bidirectional input/output signal.
AI	Input. Analog levels.
PWR	Power
GND	Ground
NC	Not Connected

**TABLE 4**  
Abbreviations for Buffer Type

Abbreviation	Description
SSTL	Serial Stub Terminated Logic (SSTL <sub>18</sub> )
LV-CMOS	Low Voltage CMOS
CMOS	CMOS Levels
OD	Open Drain. The corresponding ball has 2 operational states, active low and tristate, and allows multiple devices to share as a wire-OR.



**FIGURE 1**  
**Chip Configuration, PG-TFBGA-84 (top view)**



**Notes**

1.  $\overline{UDQS}/UDQS$  is data strobe for DQ[15:8],  $\overline{LDQS}/LDQS$  is data strobe for DQ[7:0]
2. LDM is the data mask signal for DQ[7:0], UDM is the data mask signal for DQ[15:8]
3.  $V_{DDL}$  and  $V_{SSDL}$  are power and ground for the DLL.  $V_{DDL}$  is connected to  $V_{DD}$  on the device.  $V_{DD}$ ,  $V_{DDQ}$ ,  $V_{SSDL}$ ,  $V_{SS}$  and  $V_{SSQ}$  are isolated on the device.





## 2.2 DDR2 Addressing

This chapter describes the DDR2 addressing.

**TABLE 5**  
DDR2 Addressing

Configuration	32 Mb x16 <sup>1)</sup>	Note
Bank Address	BA[1:0]	
Number of Banks	4	
Auto Precharge	A10 / AP	
Row Address	A[12:0]	
Column Address	A[9:0]	
Number of Column Address Bits	10	2)
Number of I/Os	16	
Page Size [Bytes]	2048 (2 K)	3)

1) Referred to as 'org'

2) Referred to as 'colbits'

3) PageSize =  $2^{\text{colbits}} \times \text{org}/8$  [Bytes]



### 3 Functional Description

BA1	BA0	A12	A11	A10	A9	A8	A7	A6	A5	A4	A3	A2	A1	A0
0	0	PD		WR		DLL	TM		CL		BT		BL	
reg. addr		w		w		w	w		w		w		w	

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**TABLE 6**  
Mode Register Definition (BA[1:0] = 00<sub>B</sub>)

Field	Bits	Type <sup>1)</sup>	Description
BA1	14	reg. addr.	<b>Bank Address [1]</b> 0 <sub>B</sub> <b>BA1</b> Bank Address
BA0	13		<b>Bank Address [0]</b> 0 <sub>B</sub> <b>BA0</b> Bank Address
PD	12	w	<b>Active Power-Down Mode Select</b> 0 <sub>B</sub> <b>PD</b> Fast exit 1 <sub>B</sub> <b>PD</b> Slow exit
WR	[11:9]	w	<b>Write Recovery<sup>2)</sup></b> <i>Note: All other bit combinations are illegal.</i> 001 <sub>B</sub> <b>WR</b> 2 010 <sub>B</sub> <b>WR</b> 3 011 <sub>B</sub> <b>WR</b> 4 100 <sub>B</sub> <b>WR</b> 5 101 <sub>B</sub> <b>WR</b> 6 110 <sub>B</sub> <b>WR</b> 7
DLL	8	w	<b>DLL Reset</b> 0 <sub>B</sub> <b>DLL</b> No 1 <sub>B</sub> <b>DLL</b> Yes
TM	7	w	<b>Test Mode</b> 0 <sub>B</sub> <b>TM</b> Normal Mode 1 <sub>B</sub> <b>TM</b> Vendor specific test mode
CL	[6:4]	w	<b>CAS Latency</b> <i>Note: All other bit combinations are illegal.</i> 011 <sub>B</sub> <b>CL</b> 3 100 <sub>B</sub> <b>CL</b> 4 101 <sub>B</sub> <b>CL</b> 5 110 <sub>B</sub> <b>CL</b> 6 111 <sub>B</sub> <b>CL</b> 7



HYB18T512161CF  
512-Mbit Double-Data-Rate-Two SDRAM

Field	Bits	Type <sup>1)</sup>	Description
BT	3	w	<b>Burst Type</b> 0 <sub>B</sub> <b>BT Sequential</b> 1 <sub>B</sub> <b>BT Interleaved</b>
BL	[2:0]	w	<b>Burst Length</b> <i>Note: All other bit combinations are illegal.</i> 010 <sub>B</sub> <b>BL 4</b> 011 <sub>B</sub> <b>BL 8</b>

- 1) w = write only register bits
- 2) Number of clock cycles for write recovery during auto-precharge. WR in clock cycles is calculated by dividing  $t_{WR}$  (in ns) by  $t_{CK}$  (in ns) and rounding up to the next integer:  $WR [cycles] \geq t_{WR} (ns) / t_{CK} (ns)$ . The mode register must be programmed to fulfill the minimum requirement for the analogue  $t_{WR}$  timing  $WR_{MIN}$  is determined by  $t_{CK,MAX}$  and  $WR_{MAX}$  is determined by  $t_{CK,MIN}$ .

BA1	BA0	A12	A11	A10	A9	A8	A7	A6	A5	A4	A3	A2	A1	A0
0	1	Q <sub>off</sub>	0	$\overline{DQS}$	OCD Program			R <sub>tt</sub>		AL		R <sub>tt</sub>	DIC	DLL
reg. addr				w		w		w		w		w	w	w

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**TABLE 7**  
Extended Mode Register Definition (BA[1:0] = 01<sub>B</sub>)

Field	Bits	Type <sup>1)</sup>	Description
BA1	14	reg. addr.	<b>Bank Address [1]</b> 0 <sub>B</sub> <b>BA1 Bank Address</b>
BA0	13		<b>Bank Address [0]</b> 1 <sub>B</sub> <b>BA0 Bank Address</b>
Qoff	12	w	<b>Output Disable</b> 0 <sub>B</sub> <b>QOff Output buffers enabled</b> 1 <sub>B</sub> <b>QOff Output buffers disabled</b>
A11	11	w	<b>Address Bus [11]</b> 0 <sub>B</sub> <b>A11 Address bit 11</b>
$\overline{DQS}$	10	w	<b>Complement Data Strobe (DQS Output)</b> 0 <sub>B</sub> $\overline{DQS}$ Enable 1 <sub>B</sub> $\overline{DQS}$ Disable
OCD Program	[9:7]	w	<b>Off-Chip Driver Calibration Program</b> 000 <sub>B</sub> <b>OCD</b> OCD calibration mode exit, maintain setting 001 <sub>B</sub> <b>OCD</b> Drive (1) 010 <sub>B</sub> <b>OCD</b> Drive (0) 100 <sub>B</sub> <b>OCD</b> Adjust mode 111 <sub>B</sub> <b>OCD</b> OCD calibration default

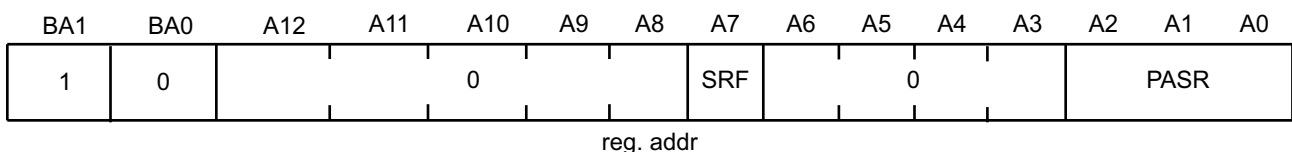


Field	Bits	Type <sup>1)</sup>	Description
AL	[5:3]	w	<b>Additive Latency</b> <i>Note: All other bit combinations are illegal.</i> 000 <sub>B</sub> AL 0 001 <sub>B</sub> AL 1 010 <sub>B</sub> AL 2 011 <sub>B</sub> AL 3 100 <sub>B</sub> AL 4 101 <sub>B</sub> AL 5 110 <sub>B</sub> AL 6
R <sub>TT</sub>	6,2	w	<b>Nominal Termination Resistance of ODT</b> <i>Note: See Table 18 "ODT DC Electrical Characteristics" on Page 18</i> 00 <sub>B</sub> R <sub>TT</sub> ∞ (ODT disabled) 01 <sub>B</sub> R <sub>TT</sub> 75 Ohm 10 <sub>B</sub> R <sub>TT</sub> 150 Ohm 11 <sub>B</sub> R <sub>TT</sub> 50 Ohm
DIC	1	w	<b>Off-chip Driver Impedance Control</b> 0 <sub>B</sub> DIC Full (Driver Size = 100%) 1 <sub>B</sub> DIC Reduced
DLL	0	w	<b>DLL Enable</b> 0 <sub>B</sub> DLL Enable 1 <sub>B</sub> DLL Disable

1) w = write only register bits

A0 is used for DLL enable or disable. A1 is used for enabling half-strength data-output driver. A2 and A6 enables On-Die termination (ODT) and sets the R<sub>tt</sub> value. A[5:3] are used for additive latency settings and A[9:7] enables the OCD impedance adjustment mode. A10 enables or disables the

differential DQS. Address bit A12 have to be set to 0 for normal operation. With A12 set to 1 the SDRAM outputs are disabled and in Hi-Z. 1 on BA0 and 0 for BA1 have to be set to access the EMRS(1).



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**TABLE 8**  
**EMRS(2) Programming Extended Mode Register Definition (BA[1:0]=10<sub>B</sub>)**

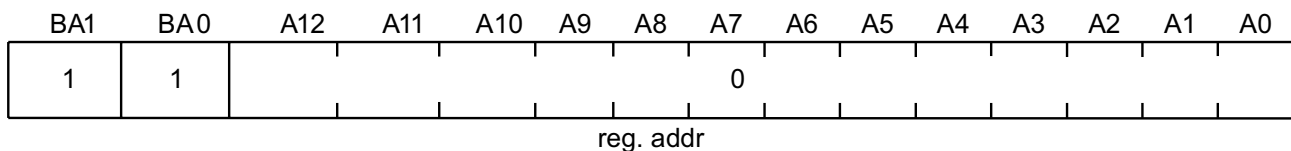
Field	Bits	Type <sup>1)</sup>	Description
BA1	14	reg. addr.,	<b>Bank Address [1]</b> 1 <sub>B</sub> BA1 Bank Address
BA0	13		<b>Bank Address [0]</b> 0 <sub>B</sub> BA0 Bank Address
A	[12:8]	w	<b>Address Bus</b> 00000 <sub>B</sub> A Address bits



HYB18T512161CF  
512-Mbit Double-Data-Rate-Two SDRAM

Field	Bits	Type <sup>1)</sup>	Description
SRF	7	w	<b>Address Bus, High Temperature Self Refresh Rate for <math>T_{CASE} &gt; 85^{\circ}C</math></b> 0 <sub>B</sub> <b>A7</b> disable 1 <sub>B</sub> <b>A7</b> enable <sup>2)</sup>
A	[6:3]	w	<b>Address Bus</b> 0000 <sub>B</sub> <b>A</b> Address bits
<b>Partial Self Refresh for 4 banks</b>			
PASR	[2:0]	w	<b>Address Bus, Partial Array Self Refresh for 4 Banks<sup>3)</sup></b> 000 <sub>B</sub> <b>PASR0</b> Full Array 001 <sub>B</sub> <b>PASR1</b> Half Array (BA[1:0]=00, 01) 010 <sub>B</sub> <b>PASR2</b> Quarter Array (BA[1:0]=00) 011 <sub>B</sub> <b>PASR3</b> Not defined 100 <sub>B</sub> <b>PASR4</b> 3/4 array (BA[1:0]=01, 10, 11) 101 <sub>B</sub> <b>PASR5</b> Half array (BA[1:0]=10, 11) 110 <sub>B</sub> <b>PASR6</b> Quarter array (BA[1:0]=11) 111 <sub>B</sub> <b>PASR7</b> Not defined

- 1) w = write only
- 2) When DRAM is operated at  $85^{\circ}C \leq T_{CASE} \leq 95^{\circ}C$  the extended self refresh rate must be enabled by setting bit A7 to "1" before the self refresh mode can be entered.
- 3) If PASR (Partial Array Self Refresh) is enabled, data located in areas of the array beyond the specified location will be lost if self refresh is entered. Data integrity will be maintained if  $t_{REF}$  conditions are met and no Self Refresh command is issued



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**TABLE 9**  
**EMR(3) Programming Extended Mode Register Definition (BA[1:0]=11<sub>B</sub>)**

Field	Bits	Type <sup>1)</sup>	Description
BA1	14	reg.addr	<b>Bank Address</b> 1 <sub>B</sub> <b>BA1</b> Bank Address
BA0	13		<b>Bank Address</b> 1 <sub>B</sub> <b>BA0</b> Bank Address
A	[12:0]	w	<b>Address Bus</b> 000000000000 <sub>B</sub> Address bits

1) w = write only



**TABLE 10**  
ODT Truth Table

Input Pin	EMRS(1) Address Bit A10	EMRS(1) Address Bit A11
DQ[7:0]	X	
DQ[15:8]	X	
LDQS	X	
$\overline{\text{LDQS}}$	0	X
UDQS	X	
$\overline{\text{UDQS}}$	0	X
LDM	X	
UDM	X	

Note: X = don't care; 0 = bit set to low; 1 = bit set to high

**TABLE 11**  
Burst Length and Sequence

Burst Length	Starting Address (A2 A1 A0)	Sequential Addressing (decimal)	Interleave Addressing (decimal)
4	× 0 0	0, 1, 2, 3	0, 1, 2, 3
	× 0 1	1, 2, 3, 0	1, 0, 3, 2
	× 1 0	2, 3, 0, 1	2, 3, 0, 1
	× 1 1	3, 0, 1, 2	3, 2, 1, 0
8	0 0 0	0, 1, 2, 3, 4, 5, 6, 7	0, 1, 2, 3, 4, 5, 6, 7
	0 0 1	1, 2, 3, 0, 5, 6, 7, 4	1, 0, 3, 2, 5, 4, 7, 6
	0 1 0	2, 3, 0, 1, 6, 7, 4, 5	2, 3, 0, 1, 6, 7, 4, 5
	0 1 1	3, 0, 1, 2, 7, 4, 5, 6	3, 2, 1, 0, 7, 6, 5, 4
	1 0 0	4, 5, 6, 7, 0, 1, 2, 3	4, 5, 6, 7, 0, 1, 2, 3
	1 0 1	5, 6, 7, 4, 1, 2, 3, 0	5, 4, 7, 6, 1, 0, 3, 2
	1 1 0	6, 7, 4, 5, 2, 3, 0, 1	6, 7, 4, 5, 2, 3, 0, 1
	1 1 1	7, 4, 5, 6, 3, 0, 1, 2	7, 6, 5, 4, 3, 2, 1, 0

**Notes**

1. Page Size and Length is a function of I/O organization:  
Page Size = 2 KByte; Page Length = 1024

2. Order of burst access for sequential addressing is “nibble-based” and therefore different from SDR or DDR components



# 4 Truth Tables

**TABLE 12**  
Command Truth Table

Function	CKE		$\overline{CS}$	$\overline{RAS}$	$\overline{CAS}$	$\overline{WE}$	BA0 BA1	A[12:11]	A10	A[9:0]	Note <sup>1)2)3)</sup>
	Previous Cycle	Current Cycle									
(Extended) Mode Register Set	H	H	L	L	L	L	BA	OP Code			4)5)
Auto-Refresh	H	H	L	L	L	H	X	X	X	X	4)
Self-Refresh Entry	H	L	L	L	L	H	X	X	X	X	4)6)
Self-Refresh Exit	L	H	H	X	X	X	X	X	X	X	4)6)7)
			L	H	H	H					
Single Bank Precharge	H	H	L	L	H	L	BA	X	L	X	4)5)
Precharge all Banks	H	H	L	L	H	L	X	X	H	X	4)
Bank Activate	H	H	L	L	H	H	BA	Row Address			4)5)
Write	H	H	L	H	L	L	BA	Column	L	Column	4)5)8)
Write with Auto-Precharge	H	H	L	H	L	L	BA	Column	H	Column	4)5)8)
Read	H	H	L	H	L	H	BA	Column	L	Column	4)5)8)
Read with Auto-Precharge	H	H	L	H	L	H	BA	Column	H	Column	4)5)8)
No Operation	H	X	L	H	H	H	X	X	X	X	4)
Device Deselect	H	X	H	X	X	X	X	X	X	X	4)
Power Down Entry	H	L	H	X	X	X	X	X	X	X	4)9)
			L	H	H	H					
Power Down Exit	L	H	H	X	X	X	X	X	X	X	4)9)
			L	H	H	H					

- 1) The state of ODT does not affect the states described in this table. The ODT function is not available during Self Refresh.
- 2) "X" means "H or L (but a defined logic level)".
- 3) Operation that is not specified is illegal and after such an event, in order to guarantee proper operation, the DRAM must be powered down and then restarted through the specified initialization sequence before normal operation can continue.
- 4) All DDR2 SDRAM commands are defined by states of  $\overline{CS}$ ,  $\overline{WE}$ ,  $\overline{RAS}$ ,  $\overline{CAS}$ , and CKE at the rising edge of the clock.
- 5) Bank addresses BA[1:0] determine which bank is to be operated upon. For (E)MRS BA[1:0] selects an (Extended) Mode Register.
- 6)  $V_{REF}$  must be maintained during Self Refresh operation.
- 7) Self Refresh Exit is asynchronous.
- 8) Burst reads or writes at BL = 4 cannot be terminated.
- 9) The Power Down Mode does not perform any refresh operations.



**TABLE 13**  
**Clock Enable (CKE) Truth Table for Synchronous Transitions**

Current State <sup>1)</sup>	CKE		Command (N) <sup>2)3)</sup> RAS, CAS, WE, CS	Action (N) <sup>2)</sup>	Note <sup>4)5)</sup>
	Previous Cycle <sup>6)</sup> (N-1)	Current Cycle <sup>6)</sup> (N)			
Power-Down	L	L	X	Maintain Power-Down	7)8)11)
	L	H	DESELECT or NOP	Power-Down Exit	7)9)10)11)
Self Refresh	L	L	X	Maintain Self Refresh	8)11)12)
	L	H	DESELECT or NOP	Self Refresh Exit	9)12)13)14)
Bank(s)Active	H	L	DESELECT or NOP	Active Power-Down Entry	7)9)10)11)15)
All Banks Idle	H	L	DESELECT or NOP	Precharge Power-Down Entry	9)10)11)15)
	H	L	AUTOREFRESH	Self Refresh Entry	7)11)14)16)
Any State other than listed above	H	H	Refer to the Command Truth Table		17)

- 1) Current state is the state of the DDR2 SDRAM immediately prior to clock edge N.
- 2) Command (N) is the command registered at clock edge N, and Action (N) is a result of Command (N)
- 3) The state of ODT does not affect the states described in this table. The ODT function is not available during Self Refresh.
- 4) CKE must be maintained HIGH while the device is in OCD calibration mode.
- 5) Operation that is not specified is illegal and after such an event, in order to guarantee proper operation, the DRAM must be powered down and then restarted through the specified initialization sequence before normal operation can continue.
- 6) CKE (N) is the logic state of CKE at clock edge N; CKE (N-1) was the state of CKE at the previous clock edge.
- 7) The Power-Down Mode does not perform any refresh operations. The duration of Power-Down Mode is therefor limited by the refresh requirements
- 8) "X" means "don't care (including floating around  $V_{REF}$ )" in Self Refresh and Power Down. However ODT must be driven HIGH or LOW in Power Down if the ODT function is enabled (Bit A2 or A6 set to "1" in EMRS(1)).
- 9) All states and sequences not shown are illegal or reserved unless explicitly described elsewhere in this document.
- 10) Valid commands for Power-Down Entry and Exit are NOP and DESELECT only.
- 11)  $t_{CKE,MIN}$  of 3 clocks means CKE must be registered on three consecutive positive clock edges. CKE must remain at the valid input level the entire time it takes to achieve the 3 clocks of registration. Thus, after any CKE transition, CKE may not transition from its valid level during the time period of  $t_{IS} + 2 \times t_{CKE} + t_{IH}$ .
- 12)  $V_{REF}$  must be maintained during Self Refresh operation.
- 13) On Self Refresh Exit DESELECT or NOP commands must be issued on every clock edge occurring during the tXSNR period. Read commands may be issued only after  $t_{XSRD}$  (200 clocks) is satisfied.
- 14) Valid commands for Self Refresh Exit are NOP and DESELCT only.
- 15) Power-Down and Self Refresh can not be entered while Read or Write operations, (Extended) mode Register operations, Precharge or Refresh operations are in progress.
- 16) Self Refresh mode can only be entered from the All Banks Idle state.
- 17) Must be a legal command as defined in the Command Truth Table.

**TABLE 14**  
**Data Mask (DM) Truth Table**

Name (Function)	DM	DQs	Note
Write Enable	L	Valid	1)
Write Inhibit	H	X	1)

- 1) Used to mask write data; provided coincident with the corresponding data.





## 5 Electrical Characteristics

This chapter describes the Electrical Characteristics.

### 5.1 Absolute Maximum Ratings

Caution is needed not to exceed absolute maximum ratings of the DRAM device listed in **Table 18** at any time.

**TABLE 15**  
Absolute Maximum Ratings

Symbol	Parameter	Rating		Unit	Note
		Min.	Max.		
$V_{DD}$	Voltage on $V_{DD}$ pin relative to $V_{SS}$	-1.0	+2.3	V	1)
$V_{DDQ}$	Voltage on $V_{DDQ}$ pin relative to $V_{SS}$	-0.5	+2.3	V	1)2)
$V_{DDL}$	Voltage on $V_{DDL}$ pin relative to $V_{SS}$	-0.5	+2.3	V	1)2)
$V_{IN}, V_{OUT}$	Voltage on any pin relative to $V_{SS}$	-0.5	+2.3	V	1)
$T_J$	Junction Temperature	-	+125	°C	1)
$T_{STG}$	Storage Temperature	-55	+150	°C	1)2)

1) When  $V_{DD}$  and  $V_{DDQ}$  and  $V_{DDL}$  are less than 500 mV;  $V_{REF}$  may be equal to or less than 300 mV.

2) Storage Temperature is the case surface temperature on the center/top side of the DRAM.

**Attention: Stresses greater than those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.**

**TABLE 16**  
DRAM Component Operating Temperature Range

Symbol	Parameter	Rating		Unit	Note
		Min.	Max.		
$T_{CASE}$	Operating Temperature	0	95	°C	1)2)3)4)

1) Operating Temperature is the case surface temperature on the center / top side of the DRAM.

2) The operating temperature range are the temperatures where all DRAM specification will be supported. During operation, the DRAM case temperature must be maintained between 0 - 95 °C under all other specification parameters.

3) Above 85 °C the Auto-Refresh command interval has to be reduced to  $t_{REF1} = 3.9 \mu s$

4) When operating this product in the 85 °C to 95 °C  $T_{CASE}$  temperature range, the High Temperature Self Refresh has to be enabled by setting EMR(2) bit A7 to “1”. When the High Temperature Self Refresh is enabled there is an increase of  $I_{DD6}$  by approximately 50%



## 5.2 DC Characteristics

**TABLE 17**  
Recommended DC Operating Conditions (SSTL\_18)

Symbol	Parameter	Rating			Unit	Notes
		Min.	Typ.	Max.		
$V_{DD}$	Supply Voltage	1.7	1.8	1.9	V	1)2)
$V_{DDDL}$	Supply Voltage for DLL	1.7	1.8	1.9	V	1)2)
$V_{DDQ}$	Supply Voltage for Output	1.7	1.8	1.9	V	1)2)
$V_{REF}$	Input Reference Voltage	$0.49 \times V_{DDQ}$	$0.5 \times V_{DDQ}$	$0.51 \times V_{DDQ}$	V	3)4)
$V_{TT}$	Termination Voltage	$V_{REF} - 0.04$	$V_{REF}$	$V_{REF} + 0.04$	V	5)

- 1) HYB18T512161CF-[16/20]
- 2)  $V_{DDQ}$  tracks with  $V_{DD}$ ,  $V_{DDDL}$  tracks with  $V_{DD}$ . AC parameters are measured with  $V_{DD}$ ,  $V_{DDQ}$  and  $V_{DDDL}$  tied together.
- 3) The value of  $V_{REF}$  may be selected by the user to provide optimum noise margin in the system. Typically the value of  $V_{REF}$  is expected to be about  $0.5 \times V_{DDQ}$  of the transmitting device and  $V_{REF}$  is expected to track variations in  $V_{DDQ}$ .
- 4) Peak to peak ac noise on  $V_{REF}$  may not exceed  $\pm 2\% V_{REF}$  (dc)
- 5)  $V_{TT}$  is not applied directly to the device.  $V_{TT}$  is a system supply for signal termination resistors, is expected to be set equal to  $V_{REF}$ , and must track variations in die dc level of  $V_{REF}$ .

**TABLE 18**  
ODT DC Electrical Characteristics

Parameter / Condition	Symbol	Min.	Nom.	Max.	Unit	Note
Termination resistor impedance value for EMRS(1)[A6,A2] = [0,1]; 75 Ohm	Rtt1(eff)	60	75	90	$\Omega$	1)
Termination resistor impedance value for EMRS(1)[A6,A2] =[1,0]; 150 Ohm	Rtt2(eff)	120	150	180	$\Omega$	1)
Termination resistor impedance value for EMRS(1)(A6,A2)=[1,1]; 50 Ohm	Rtt3(eff)	40	50	60	$\Omega$	1)
Deviation of $V_M$ with respect to $V_{DDQ} / 2$	delta $V_M$	-6.00	—	+ 6.00	%	2)

- 1) Measurement Definition for Rtt(eff): Apply  $V_{IH(ac)}$  and  $V_{IL(ac)}$  to test pin separately, then measure current  $I(V_{IH(ac)})$  and  $I(V_{IL(ac)})$  respectively.  
 $Rtt(eff) = (V_{IH(ac)} - V_{IL(ac)}) / (I(V_{IH(ac)}) - I(V_{IL(ac)}))$ .
- 2) Measurement Definition for  $V_M$ : Turn ODT on and measure voltage ( $V_M$ ) at test pin (midpoint) with no load:  $delta V_M = ((2 \times V_M / V_{DDQ}) - 1) \times 100\%$

**TABLE 19**  
Input and Output Leakage Currents

Symbol	Parameter / Condition	Min.	Max.	Unit	Notes
IIL	Input Leakage Current; any input $0 V < VIN < V_{DD}$	-2	+2	$\mu A$	1)
IOL	Output Leakage Current; $0 V < VOUT < V_{DDQ}$	-5	+5	$\mu A$	2)

- 1) all other pins not under test = 0 V
- 2) DQ's, LDQS, LDQS, UDQS, UDQS, DQS,  $\overline{DQS}$  are disabled and ODT is turned off



### 5.3 DC & AC Characteristics

DDR2 SDRAM pin timing are specified for either single ended or differential mode depending on the setting of the EMRS(1) “Enable  $\overline{DQS}$ ” mode bit; timing advantages of differential mode are realized in system design. The method by which the DDR2 SDRAM pin timing are measured is mode dependent. In single ended mode, timing relationships are measured relative to the rising or falling edges of DQS crossing at  $V_{REF}$ .

In differential mode, these timing relationships are measured relative to the crosspoint of DQS and its complement,  $\overline{DQS}$ . This distinction in timing methods is verified by design and characterization but not subject to production test. In single ended mode, the  $\overline{DQS}$  signals are internally disabled and don't care.

**TABLE 20**  
DC & AC Logic Input Levels

Symbol	Parameter	Min.	Max.	Units
$V_{IH(dc)}$	DC input logic high	$V_{REF} + 0.125$	$V_{DDQ} + 0.3$	V
$V_{IL(dc)}$	DC input low	-0.3	$V_{REF} - 0.125$	V
$V_{IH(ac)}$	AC input logic high	$V_{REF} + 0.250$	—	V
$V_{IL(ac)}$	AC input low	—	$V_{REF} - 0.250$	V

**TABLE 21**  
Single-ended AC Input Test Conditions

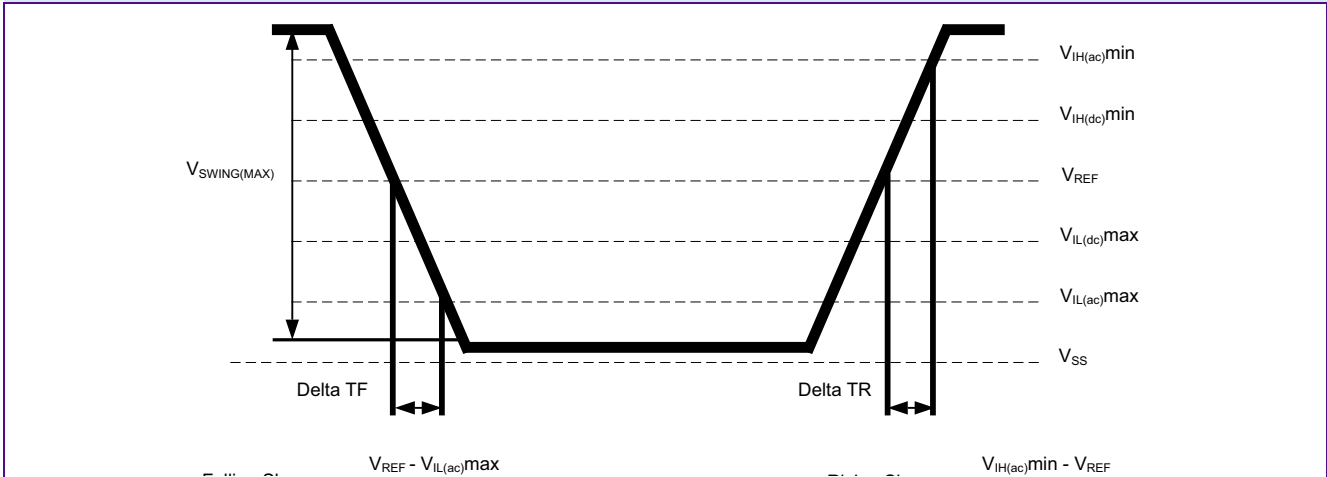
Symbol	Condition	Value	Unit	Notes
$V_{REF}$	Input reference voltage	$0.5 \times V_{DDQ}$	V	1)
$V_{SWING.MAX}$	Input signal maximum peak to peak swing	1.0	V	1)
SLEW	Input signal minimum Slew Rate	1.0	V / ns	2)3)

- 1) Input waveform timing is referenced to the input signal crossing through the  $V_{REF}$  level applied to the device under test.
- 2) The input signal minimum Slew Rate is to be maintained over the range from  $V_{IH(ac),MIN}$  to  $V_{REF}$  for rising edges and the range from  $V_{REF}$  to  $V_{IL(ac),MAX}$  for falling edges as shown in **Figure 2**
- 3) AC timings are referenced with input waveforms switching from  $V_{IL(ac)}$  to  $V_{IH(ac)}$  on the positive transitions and  $V_{IH(ac)}$  to  $V_{IL(ac)}$  on the negative transitions.



**FIGURE 2**

**Single-ended AC Input Test Conditions Diagram**



**TABLE 22**

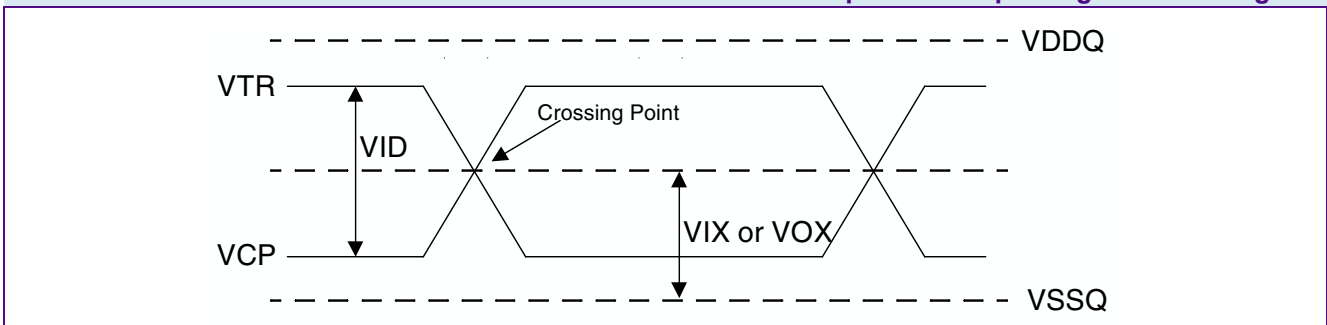
**Differential DC and AC Input and Output Logic Levels**

Symbol	Parameter	Min.	Max.	Unit	Notes
$V_{IN(dc)}$	DC input signal voltage	-0.3	$V_{DDQ} + 0.3$	—	1)
$V_{ID(dc)}$	DC differential input voltage	0.25	$V_{DDQ} + 0.6$	—	2)
$V_{ID(ac)}$	AC differential input voltage	0.5	$V_{DDQ} + 0.6$	V	3)
$V_{IX(ac)}$	AC differential cross point input voltage	$0.5 \times V_{DDQ} - 0.175$	$0.5 \times V_{DDQ} + 0.175$	V	4)
$V_{OX(ac)}$	AC differential cross point output voltage	$0.5 \times V_{DDQ} - 0.125$	$0.5 \times V_{DDQ} + 0.125$	V	5)

- 1)  $V_{IN(dc)}$  specifies the allowable DC execution of each input of differential pair such as CK, CK, DQS, DQS etc.
- 2)  $V_{ID(dc)}$  specifies the input differential voltage  $V_{TR} - V_{CP}$  required for switching. The minimum value is equal to  $V_{IH(dc)} - V_{IL(dc)}$ .
- 3)  $V_{ID(ac)}$  specifies the input differential voltage  $V_{TR} - V_{CP}$  required for switching. The minimum value is equal to  $V_{IH(ac)} - V_{IL(ac)}$ .
- 4) The value of  $V_{IX(ac)}$  is expected to equal  $0.5 \times V_{DDQ}$  of the transmitting device and  $V_{IX(ac)}$  is expected to track variations in  $V_{DDQ}$ .  $V_{IX(ac)}$  indicates the voltage at which differential input signals must cross.
- 5) The value of  $V_{OX(ac)}$  is expected to equal  $0.5 \times V_{DDQ}$  of the transmitting device and  $V_{OX(ac)}$  is expected to track variations in  $V_{DDQ}$ .  $V_{OX(ac)}$  indicates the voltage at which differential input signals must cross.

**FIGURE 3**

**Differential DC and AC Input and Output Logic Levels Diagram**





## 5.4 Output Buffer Characteristics

**TABLE 23****Full Strength Calibrated Pull-up Driver Characteristics**

Voltage (V)	Calibrated Pull-up Driver Current [mA]				
	Nominal Minimum <sup>1)</sup> (21 Ohms)	Nominal Low <sup>2)</sup> (18.75 Ohms)	Nominal (18 ohms) <sup>3)</sup>	Nominal High <sup>2)</sup> (17.25 Ohms)	Nominal Maximum <sup>4)</sup> (15 Ohms)
0.2	-9.5	-10.7	-11.4	-11.8	-13.3
0.3	-14.3	-16.0	-16.5	-17.4	-20.0
0.4	-18.3	-21.0	-21.2	-23.0	-27.0

- 1) The driver characteristics evaluation conditions are Nominal Minimum 95 °C ( $T_{CASE}$ ),  $V_{DDQ} = 1.7$  V, any process
- 2) The driver characteristics evaluation conditions are Nominal Low and Nominal High 25 °C ( $T_{CASE}$ ),  $V_{DDQ} = 1.8$  V, any process
- 3) The driver characteristics evaluation conditions are Nominal 25 °C ( $T_{CASE}$ ),  $V_{DDQ} = 1.8$  V, typical process
- 4) The driver characteristics evaluation conditions are Nominal Maximum 0 °C ( $T_{CASE}$ ),  $V_{DDQ} = 1.9$  V, any process

**TABLE 24****Full Strength Calibrated Pull-down Driver Characteristics**

Voltage (V)	Calibrated Pull-down Driver Current [mA]				
	Nominal Minimum <sup>1)</sup> (21 Ohms)	Nominal Low <sup>2)</sup> (18.75 Ohms)	Nominal <sup>3)</sup> (18 ohms)	Nominal High <sup>2)</sup> (17.25 Ohms)	Nominal Maximum <sup>4)</sup> (15 Ohms)
0.2	9.5	10.7	11.5	11.8	13.3
0.3	14.3	16.0	16.6	17.4	20.0
0.4	18.7	21.0	21.6	23.0	27.0

- 1) The driver characteristics evaluation conditions are Nominal Minimum 95 °C ( $T_{CASE}$ ),  $V_{DDQ} = 1.7$  V, any process
- 2) The driver characteristics evaluation conditions are Nominal Low and Nominal High 25 °C ( $T_{CASE}$ ),  $V_{DDQ} = 1.8$  V any process
- 3) The driver characteristics evaluation conditions are Nominal 25 °C ( $T_{CASE}$ ),  $V_{DDQ} = 1.8$  V, typical process
- 4) The driver characteristics evaluation conditions are Nominal Maximum 0 °C ( $T_{CASE}$ ),  $V_{DDQ} = 1.9$  V, any process



## 5.5 Input / Output Capacitance

**TABLE 25**  
Input / Output Capacitance

Symbol	Parameter	Min.	Max.	Unit
CCK	Input capacitance, CK and $\overline{\text{CK}}$	1.0	2.0	pF
CDCK	Input capacitance delta, CK and $\overline{\text{CK}}$	—	0.25	pF
CI	Input capacitance, all other input-only pins	1.0	1.75	pF
CDI	Input capacitance delta, all other input-only pins	—	0.25	pF
CIO	Input/output capacitance, DQ, DM, DQS, $\overline{\text{DQS}}$	2.5	3.5	pF
CDIO	Input/output capacitance delta, DQ, DM, DQS, $\overline{\text{DQS}}$	—	0.5	pF

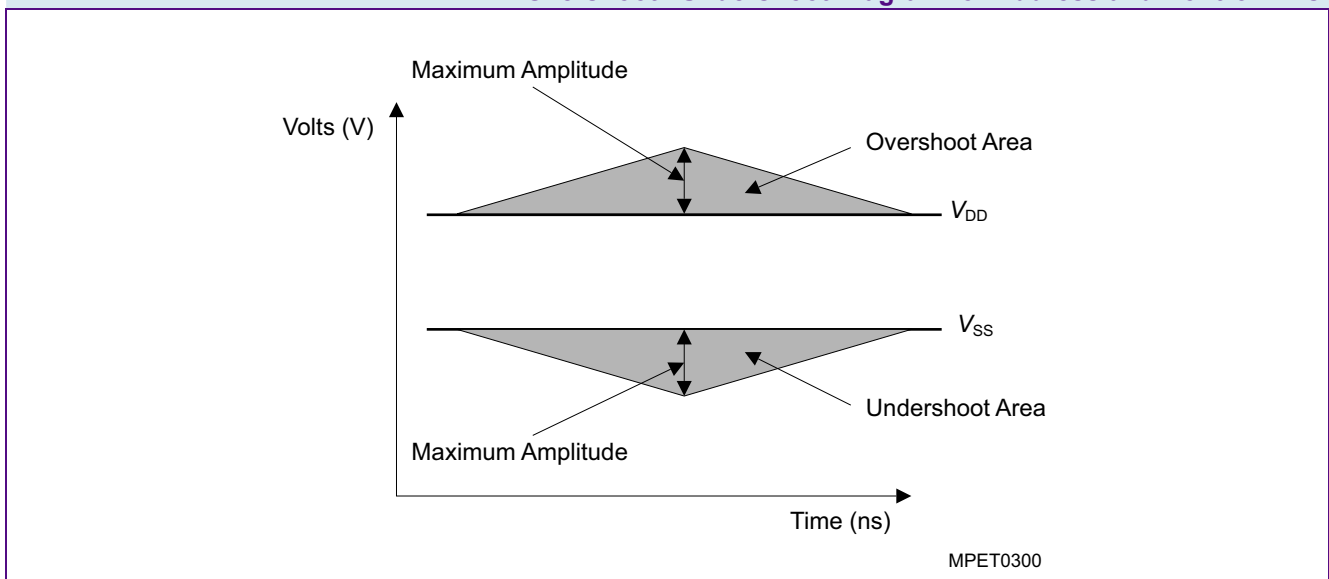


## 5.6 Overshoot and Undershoot Specification

**TABLE 26**  
AC Overshoot / Undershoot Specification for Address and Control Pins

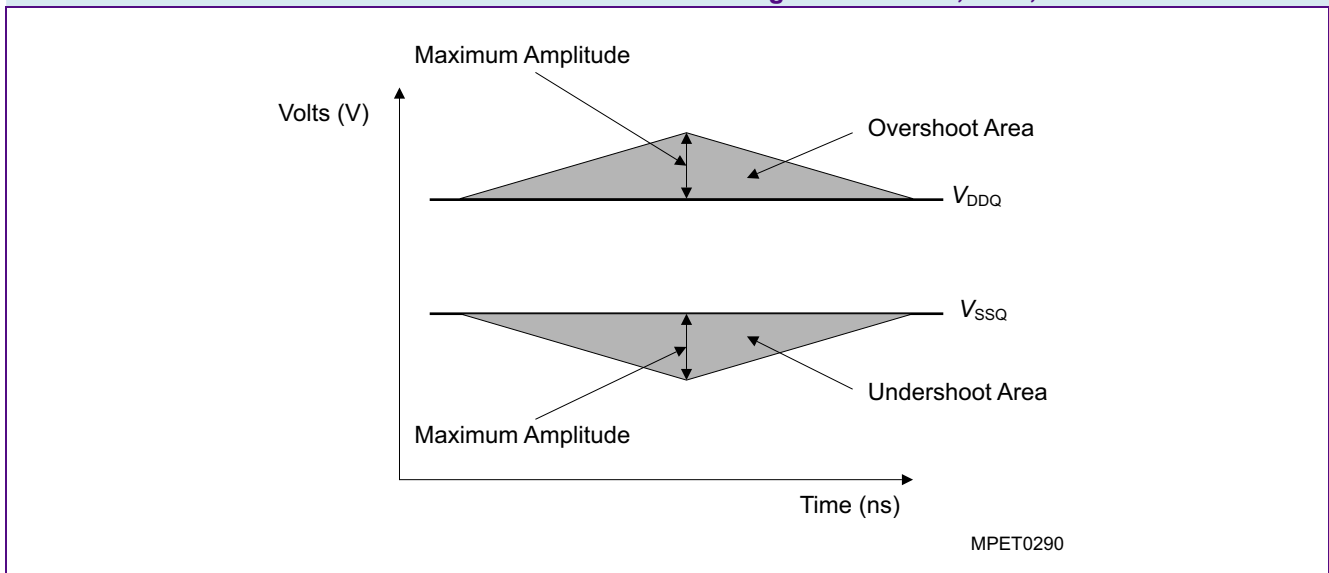
Parameter	-16	-20	Unit
Maximum peak amplitude allowed for overshoot area	0.5	0.5	V
Maximum peak amplitude allowed for undershoot area	0.5	0.5	V
Maximum overshoot area above $V_{DD}$	0.80	0.80	V.ns
Maximum undershoot area below $V_{SS}$	0.80	0.80	V.ns

**FIGURE 4**  
AC Overshoot / Undershoot Diagram for Address and Control Pins



**TABLE 27**  
**AC Overshoot / Undershoot Specification for Clock, Data, Strobe and Mask Pins**

Parameter	-16	-20	Unit
Maximum peak amplitude allowed for overshoot area	0.9	0.9	V
Maximum peak amplitude allowed for undershoot area	0.9	0.9	V
Maximum overshoot area above $V_{DDQ}$	0.23	0.23	V.ns
Maximum undershoot area below $V_{SSQ}$	0.23	0.23	V.ns

**FIGURE 5**  
**AC Overshoot / Undershoot Diagram for Clock, Data, Strobe and Mask Pins**





## 5.7 AC Characteristics

### 5.7.1 Speed Grade Definitions

**TABLE 28**  
Speed Grade Definition

Speed Grade		Symbol	-16		-20		Unit	Note
Parameter			Min.	Max.	Min.	Max.		
Clock Frequency	@ CL = 3	$t_{CK}$	5	8	5	8	ns	1)2)3)4)
	@ CL = 4	$t_{CK}$	3.75	8	3.75	8	ns	1)2)3)4)
	@ CL = 5	$t_{CK}$	3	8	3	8	ns	1)2)3)4)
	@ CL = 6	$t_{CK}$	2.5	8	2.5	8	ns	1)2)3)4)
	@ CL = 7	$t_{CK}$	1.66	8	2.0	8	ns	1)2)3)4)
Row Active Time		$t_{RAS}$	45	70k	45	70k	ns	1)2)3)4)5)
Row Cycle Time		$t_{RC}$	60	—	60	—	ns	1)2)3)4)
RAS-CAS-Delay		$t_{RCD}$	15	—	15	—	ns	1)2)3)4)
Row Precharge Time		$t_{RP}$	15	—	15	—	ns	1)2)3)4)

- 1) Timings are guaranteed with CK/CK differential Slew Rate of 2.0 V/ns. For DQS signals timings are guaranteed with a differential Slew Rate of 2.0 V/ns in differential strobe mode and a Slew Rate of 1 V/ns in single ended mode. Timings are further guaranteed for normal OCD drive strength (EMRS(1) A1 = 0) under the "Reference Load for Timing Measurements".
- 2) The CK/CK input reference level (for timing reference to CK/CK) is the point at which CK and CK cross. The DQS / DQS, input reference level is the crosspoint when in differential strobe mode.
- 3) Inputs are not recognized as valid until  $V_{REF}$  stabilizes. During the period before  $V_{REF}$  stabilizes,  $CKE = 0.2 \times V_{DDQ}$  is recognized as low.
- 4) The output timing reference voltage level is  $V_{TT}$ .
- 5)  $t_{RAS,MAX}$  is calculated from the maximum amount of time a DDR2 device can operate without a refresh command which is equal to  $9 \times t_{REFI}$ .



## 5.7.2 AC Timing Parameters

List of Timing Parameters

**TABLE 29**  
Timing Parameter by Speed Grade

Parameter	Symbol	-16		-20		Unit	Notes <sup>1)</sup> 2)3)4)5)6)
		Min.	Max.	Min.	Max.		
DQ output access time from CK / $\overline{CK}$	$t_{AC}$	-400	+400	-450	+450	ps	
CAS A to CAS B command period	$t_{CCD}$	2	—	2	—	$t_{CK}$	
CK, $\overline{CK}$ high-level width	$t_{CH}$	0.45	0.55	0.45	0.55	$t_{CK}$	
CKE minimum high and low pulse width	$t_{CKE}$	3	—	3	—	$t_{CK}$	
CK, $\overline{CK}$ low-level width	$t_{CL}$	0.45	0.55	0.45	0.55	$t_{CK}$	
Auto-Precharge write recovery + precharge time	$t_{DAL}$	WR + $t_{RP}$	—	WR + $t_{RP}$	—	$t_{CK}$	7)18)
Minimum time clocks remain ON after CKE asynchronously drops LOW	$t_{DELAY}$	$t_{IS} + t_{CK} + t_{IH}$	—	$t_{IS} + t_{CK} + t_{IH}$	—	ns	8)
DQ and DM input hold time (differential data strobe)	$t_{DH}$	90	—	145	—	ps	9)
DQ and DM input hold time (single ended data strobe)	$t_{DH1}$	-160	—	-105	—	ps	9)
DQ and DM input pulse width (each input)	$t_{DIPW}$	0.35	—	0.35	—	$t_{CK}$	
DQS output access time from CK / $\overline{CK}$	$t_{DQSCK}$	-400	+400	-450	+450	ps	9)
DQS input low (high) pulse width (write cycle)	$t_{DQSL,H}$	0.35	—	0.35	—	$t_{CK}$	
DQS-DQ skew (for DQS & associated DQ signals)	$t_{DQSQ}$	—	280	—	280	ps	10)
Write command to 1st DQS latching transition	$t_{DQSS}$	WL - 0.25	WL + 0.25	WL - 0.25	WL + 0.25	$t_{CK}$	
DQ and DM input setup time (differential data strobe)	$t_{DS}$	-35	—	20	—	ps	9)
DQ and DM input setup time (single ended data strobe)	$t_{DS1}$	-160	—	-105	—	ps	9)
DQS falling edge hold time from CK (write cycle)	$t_{DSH}$	0.2	—	0.2	—	$t_{CK}$	
DQS falling edge to CK setup time (write cycle)	$t_{DSS}$	0.2	—	0.2	—	$t_{CK}$	
Clock half period	$t_{HP}$	MIN. ( $t_{CL}$ , $t_{CH}$ )	—	MIN. ( $t_{CL}$ , $t_{CH}$ )	—		11)
Data-out high-impedance time from CK / $\overline{CK}$	$t_{HZ}$	—	$t_{AC,MAX}$	—	$t_{AC,MAX}$	ps	12)
Address and control input hold time	$t_{IH}$	475	—	525	—	ps	
Address and control input pulse width (each input)	$t_{IPW}$	0.6	—	0.6	—	$t_{CK}$	
Address and control input setup time	$t_{IS}$	350	—	400	—	ps	
DQ low-impedance time from CK / $\overline{CK}$	$t_{LZ(DQ)}$	$2 \times t_{AC,MIN}$	$t_{AC,MAX}$	$2 \times t_{AC,MIN}$	$t_{AC,MAX}$	ps	12)
DQS low-impedance from CK / $\overline{CK}$	$t_{LZ(DQS)}$	$t_{AC,MIN}$	$t_{AC,MAX}$	$t_{AC,MIN}$	$t_{AC,MAX}$	ps	12)
Mode register set command cycle time	$t_{MRD}$	2	—	2	—	$t_{CK}$	
OCD drive mode output delay	$t_{OIT}$	0	12	0	12	ns	
Data output hold time from DQS	$t_{QH}$	$t_{HP} - t_{QHS}$	—	$t_{HP} - t_{QHS}$	—		



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512-Mbit Double-Data-Rate-Two SDRAM

Parameter	Symbol	-16		-20		Unit	Notes <sup>1)</sup> 2)3)4)5)6)
		Min.	Max.	Min.	Max.		
Data hold skew factor	$t_{QHS}$	—	380	—	380	ps	
Average periodic refresh Interval	$t_{REFI}$	—	7.8	—	7.8	$\mu s$	13)14)
		—	3.9	—	3.9	$\mu s$	13)15)
Auto-Refresh to Active/Auto-Refresh command period	$t_{RFC}$	105	—	105	—	ns	16)
Read preamble	$t_{RPRE}$	0.9	1.1	0.9	1.1	$t_{CK}$	12)
Read postamble	$t_{RPST}$	0.40	0.60	0.40	0.60	$t_{CK}$	12)
Active bank A to Active bank B command period	$t_{RRD}$	10	—	10	—	ns	14)17)
Internal Read to Precharge command delay	$t_{RTP}$	7.5	—	7.5	—	ns	
Write preamble	$t_{WPRE}$	$0.35 \times t_{CK}$	—	$0.35 \times t_{CK}$	—	$t_{CK}$	
Write postamble	$t_{WPST}$	0.40	0.60	0.40	0.60	$t_{CK}$	17)
Write recovery time for write without Auto-Precharge	$t_{WR}$	11.6	—	14	—	ns	
Write recovery time for write with Auto-Precharge	WR	$t_{WR}/t_{CK}$	—	$t_{WR}/t_{CK}$	—	$t_{CK}$	18)
Internal Write to Read command delay	$t_{WTR}$	7.5	—	7.5	—	ns	19)
Exit power down to any valid command (other than NOP or Deselect)	$t_{XARD}$	2	—	2	—	$t_{CK}$	20)
Exit active power-down mode to Read command (slow exit, lower power)	$t_{XARDS}$	10 – AL	—	10 – AL	—	$t_{CK}$	20)
Exit precharge power-down to any valid command (other than NOP or Deselect)	$t_{XP}$	2	—	2	—	$t_{CK}$	
Exit Self-Refresh to non-Read command	$t_{XSNR}$	$t_{RFC} + 10$	—	$t_{RFC} + 10$	—	ns	
Exit Self-Refresh to Read command	$t_{XSRD}$	200	—	200	—	$t_{CK}$	

- 1)  $V_{DDQ}$ ,  $V_{DD}$  refer to **Chapter 1**.
- 2) Timing that is not specified is illegal and after such an event, in order to guarantee proper operation, the DRAM must be powered down and then restarted through the specified initialization sequence before normal operation can continue.
- 3) Timings are guaranteed with CK/ $\overline{CK}$  differential Slew Rate of 2.0 V/ns. For DQS signals timings are guaranteed with a differential Slew Rate of 2.0 V/ns in differential strobe mode and a Slew Rate of 1 V/ns in single ended mode. For other Slew Rates see **Chapter 5** of this data sheet.
- 4) The CK /  $\overline{CK}$  input reference level (for timing reference to CK /  $\overline{CK}$ ) is the point at which CK and  $\overline{CK}$  cross. The DQS /  $\overline{DQS}$  input reference level is the crosspoint when in differential strobe mode; The input reference level for signals other than CK/ $\overline{CK}$ , DQS /  $\overline{DQS}$  is defined in **Chapter 5.3** of this data sheet.
- 5) Inputs are not recognized as valid until  $V_{REF}$  stabilizes. During the period before  $V_{REF}$  stabilizes,  $CKE = 0.2 \times V_{DDQ}$  is recognized as low.
- 6) The output timing reference voltage level is  $V_{TT}$ . See **Chapter 5** for the reference load for timing measurements.
- 7) For each of the terms, if not already an integer, round to the next highest integer.  $t_{CK}$  refers to the application clock period. WR refers to the WR parameter stored in the MR.
- 8) The clock frequency is allowed to change during self-refresh mode or precharge power-down mode. In case of clock frequency change during power-down, a specific procedure is required.
- 9) Timing is referenced to Industrial standard definition
- 10) Consists of data pin skew and output pattern effects, and p-channel to n-channel variation of the output drivers as well as output Slew Rate mis-match between DQS /  $\overline{DQS}$  and associated DQ in any given cycle.
- 11) MIN ( $t_{CL}$ ,  $t_{CH}$ ) refers to the smaller of the actual clock low time and the actual clock high time as provided to the device (i.e. this value can be greater than the minimum specification limits for  $t_{CL}$  and  $t_{CH}$ ).
- 12) The  $t_{HZ}$ ,  $t_{RPST}$  and  $t_{LZ}$ ,  $t_{RPRE}$  parameters are referenced to a specific voltage level, which specify when the device output is no longer driving ( $t_{HZ}$ ,  $t_{RPST}$ ), or begins driving ( $t_{LZ}$ ,  $t_{RPRE}$ ).  $t_{HZ}$  and  $t_{LZ}$  transitions occur in the same access time windows as valid data transitions. These parameters are verified by design and characterization, but not subject to production test.



HYB18T512161CF  
512-Mbit Double-Data-Rate-Two SDRAM

- 13) The Auto-Refresh command interval has be reduced to 3.9  $\mu$ s when operating the DDR2 DRAM in a temperature range between 85 °C and 95 °C.
- 14) 0 °C  $\leq T_{CASE} \leq 85$  °C
- 15) 85 °C  $< T_{CASE} \leq 95$  °C
- 16) A maximum of eight Auto-Refresh commands can be posted to any given DDR2 SDRAM device.
- 17) The maximum limit for the  $t_{WPST}$  parameter is not a device limit. The device operates with a greater value for this parameter, but system performance (bus turnaround) degrades accordingly.
- 18) WR must be programmed to fulfill the minimum requirement for the  $t_{WR}$  timing parameter, where  $WR_{MIN}[\text{cycles}] = t_{WR}(\text{ns})/t_{CK}(\text{ns})$  rounded up to the next integer value.  $t_{DAL} = WR + (t_{RP}/t_{CK})$ . For each of the terms, if not already an integer, round to the next highest integer.  $t_{CK}$  refers to the application clock period. WR refers to the WR parameter stored in the MRS.
- 19) Minimum  $t_{WTR}$  is two clocks when operating the DDR2-SDRAM at frequencies  $\leq 200$  MHz.
- 20) User can choose two different active power-down modes for additional power saving via MRS address bit A12. In "standard active power-down mode" (MR, A12 = "0") a fast power-down exit timing  $t_{XARD}$  can be used. In "low active power-down mode" (MR, A12 ="1") a slow power-down exit timing  $t_{XARDS}$  has to be satisfied.

### 5.7.3 ODT AC Electrical Characteristics

**TABLE 30**  
ODT AC Characteristics and Operating Conditions for all bins

Symbol	Parameter / Condition	Values		Unit	Note
		Min.	Max.		
$t_{AOND}$	ODT turn-on delay	2	2	$n_{CK}$	1)
$t_{AON}$	ODT turn-on	$t_{AC.MIN}$	$t_{AC.MAX} + 0.7$ ns	ns	1)2)
$t_{AONPD}$	ODT turn-on (Power-Down Modes)	$t_{AC.MIN} + 2$ ns	$2 t_{CK} + t_{AC.MAX} + 1$ ns	ns	1)
$t_{AOFD}$	ODT turn-off delay	2.5	2.5	$n_{CK}$	1)
$t_{AOF}$	ODT turn-off	$t_{AC.MIN}$	$t_{AC.MAX} + 0.6$ ns	ns	1)3)
$t_{AOFPD}$	ODT turn-off (Power-Down Modes)	$t_{AC.MIN} + 2$ ns	$2.5 t_{CK} + t_{AC.MAX} + 1$ ns	ns	1)
$t_{ANPD}$	ODT to Power Down Mode Entry Latency	3	—	$n_{CK}$	1)
$t_{AXPD}$	ODT Power Down Exit Latency	8	—	$n_{CK}$	1)

- 1) Unit " $t_{CK.AVG}$ " represents the actual  $t_{CK.AVG}$  of the input clock under operation. Unit " $n_{CK}$ " represents one clock cycle of the input clock, counting the actual clock edges. Example:  $t_{XP} = 2 [n_{CK}]$  means; if Power Down exit is registered at  $T_m$ , an Active command may be registered at  $T_m + 2$ , even if  $(T_m + 2 - T_m)$  is  $2 \times t_{CK.AVG} + t_{ERR.2PER(Min)}$ .
- 2) ODT turn on time min is when the device leaves high impedance and ODT resistance begins to turn on. ODT turn on time max is when the ODT resistance is fully on. Both are measured from  $t_{AOND}$ , which is interpreted differently per speed bin.  $t_{AOND}$  is 2 clock cycles after the clock edge that registered a first ODT HIGH counting the actual input clock edges.
- 3) ODT turn off time min is when the device starts to turn off ODT resistance. ODT turn off time max is when the bus is in high impedance. Both are measured from  $t_{AOFD}$ , which is interpreted differently per speed bin. If  $t_{CK(avg)} = 3$  ns is assumed,  $t_{AOFD}$  is 1.5 ns (= 0.5 x 3 ns) after the second trailing clock edge counting from the clock edge that registered a first ODT LOW and by counting the actual input clock edges.



# 6 Currents Measurement Conditions

**TABLE 31**  
 **$I_{DD}$  Measurement Conditions**

Parameter	Symbol	Note
<b>Operating Current - One bank Active - Precharge</b> $t_{CK} = t_{CK(1DD)}$ ; $t_{RC} = t_{RC(1DD)}$ ; $t_{RAS} = t_{RAS.MIN(1DD)}$ , $\overline{CS}$ is HIGH, $\overline{CS}$ is HIGH between valid commands. Address and control inputs are switching; Databus inputs are switching.	$I_{DD0}$	1)2)3)4)5)6)7)
<b>Operating Current - One bank Active - Read - Precharge</b> $I_{OUT} = 0$ mA, $BL = 4$ , $t_{CK} = t_{CK(1DD)}$ ; $t_{RC} = t_{RC(1DD)}$ ; $t_{RAS} = t_{RAS.MIN(1DD)}$ ; $t_{RCD} = t_{RCD(1DD)}$ , $AL = 0$ , $CL = CL(1DD)$ ; $\overline{CS}$ is HIGH, $\overline{CS}$ is HIGH between valid commands. Address and control inputs are switching; Databus inputs are switching.	$I_{DD1}$	1)2)3)4)5)6)7)
<b>Precharge Power-Down Current</b> All banks idle; $\overline{CS}$ is LOW; $t_{CK} = t_{CK(1DD)}$ ; Other control and address inputs are stable; Data bus inputs are floating.	$I_{DD2P}$	1)2)3)4)5)6)7)
<b>Precharge Standby Current</b> All banks idle; $\overline{CS}$ is HIGH; $\overline{CS}$ is HIGH; $t_{CK} = t_{CK(1DD)}$ ; Other control and address inputs are switching, Data bus inputs are switching.	$I_{DD2N}$	1)2)3)4)5)6)7)
<b>Precharge Quiet Standby Current</b> All banks idle; $\overline{CS}$ is HIGH; $\overline{CS}$ is HIGH; $t_{CK} = t_{CK(1DD)}$ ; Other control and address inputs are stable, Data bus inputs are floating.	$I_{DD2Q}$	1)2)3)4)5)6)7)
<b>Active Power-Down Current</b> All banks open; $t_{CK} = t_{CK(1DD)}$ , $\overline{CS}$ is LOW; Other control and address inputs are stable; Data bus inputs are floating. MRS A12 bit is set to "0" (Fast Power-down Exit).	$I_{DD3P(0)}$	1)2)3)4)5)6)7)
<b>Active Power-Down Current</b> All banks open; $t_{CK} = t_{CK(1DD)}$ , $\overline{CS}$ is LOW; Other control and address inputs are stable, Data bus inputs are floating. MRS A12 bit is set to 1 (Slow Power-down Exit);	$I_{DD3P(1)}$	1)2)3)4)5)6)7)
<b>Active Standby Current</b> All banks open; $t_{CK} = t_{CK(1DD)}$ ; $t_{RAS} = t_{RAS.MAX(1DD)}$ ; $t_{RP} = t_{RP(1DD)}$ ; $\overline{CS}$ is HIGH, $\overline{CS}$ is HIGH between valid commands. Address inputs are switching; Data Bus inputs are switching;	$I_{DD3N}$	1)2)3)4)5)6)7)
<b>Operating Current</b> Burst Read: All banks open; Continuous burst reads; $BL = 4$ ; $AL = 0$ , $CL = CL(1DD)$ ; $t_{CK} = t_{CK(1DD)}$ ; $t_{RAS} = t_{RAS.MAX(1DD)}$ ; $t_{RP} = t_{RP(1DD)}$ ; $\overline{CS}$ is HIGH, $\overline{CS}$ is HIGH between valid commands. Address inputs are switching; Data Bus inputs are switching; $I_{OUT} = 0$ mA.	$I_{DD4R}$	1)2)3)4)5)6)7)
<b>Operating Current</b> Burst Write: All banks open; Continuous burst writes; $BL = 4$ ; $AL = 0$ , $CL = CL(1DD)$ ; $t_{CK} = t_{CK(1DD)}$ ; $t_{RAS} = t_{RAS.MAX(1DD)}$ ; $t_{RP} = t_{RP(1DD)}$ ; $\overline{CS}$ is HIGH, $\overline{CS}$ is HIGH between valid commands. Address inputs are switching; Data Bus inputs are switching;	$I_{DD4W}$	1)2)3)4)5)6)7)
<b>Burst Refresh Current</b> $t_{CK} = t_{CK(1DD)}$ , Refresh command every $t_{RFC} = t_{RFC(1DD)}$ interval, $\overline{CS}$ is HIGH, $\overline{CS}$ is HIGH between valid commands, Other control and address inputs are switching, Data bus inputs are switching.	$I_{DD5B}$	1)2)3)4)5)6)7)
<b>Distributed Refresh Current</b> $t_{CK} = t_{CK(1DD)}$ , Refresh command every $t_{REFI} = 7.8$ $\mu$ s interval, $\overline{CS}$ is LOW and $\overline{CS}$ is HIGH between valid commands, Other control and address inputs are switching, Data bus inputs are switching.	$I_{DD5D}$	1)2)3)4)5)6)7)



HYB18T512161CF  
512-Mbit Double-Data-Rate-Two SDRAM

Parameter	Symbol	Note
<b>Self-Refresh Current</b> CKE $\leq$ 0.2 V; external clock off, CK and $\overline{\text{CK}}$ at 0 V; Other control and address inputs are floating, Data bus inputs are floating.	$I_{\text{DD6}}$	1)2)3)4)5)6)7)
<b>Operating Bank Interleave Read Current</b> All banks interleaving reads, $I_{\text{OUT}} = 0$ mA; BL = 4, CL = CL <sub>(IDD)</sub> , AL = $t_{\text{RCD(IDD)}} - 1 \times t_{\text{CK(IDD)}}$ ; $t_{\text{CK}} = t_{\text{CK(IDD)}}$ ; $t_{\text{RC}} = t_{\text{RC(IDD)}}$ ; $t_{\text{RRD}} = t_{\text{RRD(IDD)}}$ ; CKE is HIGH, $\overline{\text{CS}}$ is HIGH between valid commands. Address bus inputs are stable during deselects; Data bus is switching.	$I_{\text{DD7}}$	1)2)3)4)5)6)7)8)

- 1)  $V_{\text{DDQ}} = 1.8 \text{ V} \pm 0.1 \text{ V}$ ;  $V_{\text{DD}} = 1.8 \text{ V} \pm 0.1 \text{ V}$ ;
- 2) HYB18T512161CF-16/20
- 3)  $I_{\text{DD}}$  specifications are tested after the device is properly initialized
- 4)  $I_{\text{DD}}$  parameter are specified with ODT disabled
- 5) Data Bus consists of DQ, DM, DQS,  $\overline{\text{DQS}}$ , LDQS,  $\overline{\text{LDQS}}$ , UDQS and  $\overline{\text{UDQS}}$
- 6) Definitions for  $I_{\text{DD}}$ : see **Table 32**
- 7) Timing parameter minimum and maximum values for  $I_{\text{DD}}$  current measurements
- 8) A = Activate, RA = Read with Auto-Precharge, D=DESELECT

**TABLE 32**  
Definition for  $I_{\text{DD}}$

Parameter	Description
LOW	defined as $V_{\text{IN}} \leq V_{\text{IL(ac).MAX}}$
HIGH	defined as $V_{\text{IN}} \geq V_{\text{IH(ac).MIN}}$
STABLE	defined as inputs are stable at a HIGH or LOW level
FLOATING	defined as inputs are $V_{\text{REF}} = V_{\text{DDQ}} / 2$
SWITCHING	defined as: Inputs are changing between high and low every other clock (once per two clocks) for address and control signals, and inputs changing between high and low every other clock (once per clock) for DQ signals not including mask or stobes



**TABLE 33**  
 **$I_{DD}$  Specification**

Speed Grade	-16	-20	Unit	Note
Symbol	typ	typ.		
$I_{DD0}$	93	84	mA	
$I_{DD1}$	101	92	mA	
$I_{DD2P}$	6	6	mA	
$I_{DD2N}$	60	53	mA	
$I_{DD2Q}$	58	51	mA	
$I_{DD3P(0)}$	27	23	mA	1)
$I_{DD3P(1)}$	8	8	mA	2)
$I_{DD3N}$	67	60	mA	
$I_{DD4R}$	221	189	mA	
$I_{DD4W}$	206	177	mA	
$I_{DD5B}$	122	115	mA	
$I_{DD5D}$	7	7	mA	3)
$I_{DD6}$	4	4	mA	3)
$I_{DD7}$	197	190	mA	

- 1) MRS(12)=0
- 2) MRS(12)=1
- 3)  $0^{\circ}\text{C} \leq T_{\text{CASE}} \leq 85^{\circ}\text{C}$

## 6.1 $I_{DD}$ Test Conditions

For testing the  $I_{DD}$  parameters, the following timing parameters are used:

**TABLE 34**  
 **$I_{DD}$  Measurement Test Condition**

Parameter	Symbol	-16	-20	Unit	Notes	
CAS Latency	$CL_{IDD}$	7	7	$t_{CK}$		
Clock Cycle Time	$t_{CKIDD}$	1.66	2.0	ns		
Active to Read or Write delay	$t_{RCD.IDD}$	15	15	ns		
Active to Active / Auto-Refresh command period	$t_{RC.IDD}$	60	60	ns		
Active bank A to Active bank B command delay	$t_{RRD.IDD}$	10	10	ns	1)	
Active to Precharge Command	$t_{RAS.MIN.IDD}$	45	45	ns		
	$t_{RAS.MAX.IDD}$	70k	70k	ns		
Precharge Command Period	$t_{RP.IDD}$	15	15	ns		
Auto-Refresh to Active / Auto-Refresh command period	$t_{RFC.IDD}$	105	105	ns		
Average periodic Refresh interval	$t_{REFI}$	$0^{\circ}\text{C} \leq T_{\text{CASE}} \leq 85^{\circ}\text{C}$	7.8	7.8	$\mu\text{s}$	
		$85^{\circ}\text{C} \leq T_{\text{CASE}} \leq 95^{\circ}\text{C}$	3.9	3.9	$\mu\text{s}$	

- 1) 2 kB page size



## 6.1.1 On Die Termination (ODT) Current

The ODT function adds additional current consumption to the DDR2 SDRAM when enabled by the EMRS(1). Depending on address bits A6 & A2 in the EMRS(1) a “weak” or “strong” termination can be selected. The current consumption for any terminated input pin depends on whether the input pin is in tri-state or driving “0” or “1”, as long a ODT is enabled during a given period of time. See [Table 35](#)

**TABLE 35**  
ODT current per terminated input pin

ODT Current		EMRS(1) State	Min.	Typ.	Max.	Unit
<b>Enabled ODT current per DQ</b> added $I_{DDQ}$ current for ODT enabled;ODT is HIGH; Data Bus inputs are floating	$I_{ODTO}$	A6 = 0, A2 = 1	5	6	7.5	mA/DQ
		A6 = 1, A2 = 0	2.5	3	3.75	mA/DQ
		A6 = 1, A2 = 1	7.5	9	11.25	mA/DQ
<b>Active ODT current per DQ</b> added $I_{DDQ}$ current for ODT enabled;ODT is HIGH; worst case of Data Bus inputs are stable or switching.	$I_{ODTT}$	A6 = 0, A2 = 1	10	12	15	mA/DQ
		A6 = 1, A2 = 0	5	6	7.5	mA/DQ
		A6 = 1, A2 = 1	15	18	22.5	mA/DQ

*Note: For power consumption calculations the ODT duty cycle has to be taken into account*

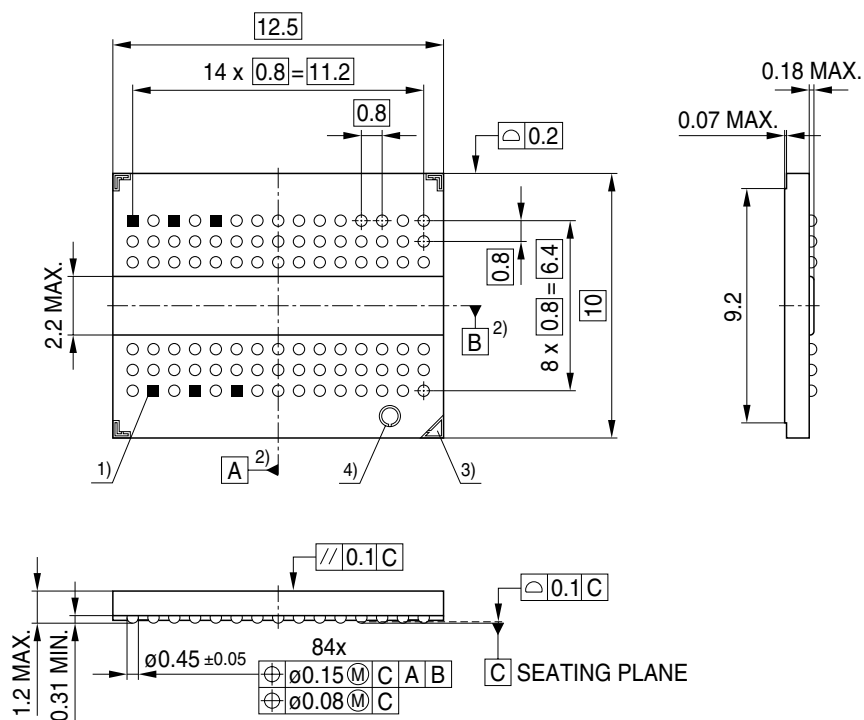




# 7 Package

## 7.1 Package Dimension

**FIGURE 6**  
Package Outline P(G)-TFBGA-84



- 1) Dummy pads without ball ■
- 2) Middle of packages edges
- 3) Package orientation mark A1
- 4) Bad unit marking (BUM)

FPO\_PG-TFBGA\_\_084-053

### Notes

1. Drawing according to ISO 8015
2. Dimensions in mm
3. General tolerances +/- 0.15

HYB18T512161CF  
512-Mbit Double-Data-Rate-Two SDRAM

## 7.2 Package Thermal Characteristics

**TABLE 36**  
Package thermal characteristics

JESD51	Theta_jA <sup>1)</sup>						Theta_jC <sup>2)</sup>
JEDEC Board	1s0p			2s0p			
Air Flow	0 m/s	1 m/s	3 m/s	0 m/s	1 m/s	3 m/s	
Rth[K/W]	69	53	47	41	35	33	5

1) Junction to Ambient thermal resistance. The value has been obtained by simulation using the conditions stated in the Industrial standard.

2) Junction to Case thermal resistance. The value has been obtained by simulation.



# List of Illustrations

Figure 1	Chip Configuration, PG-TFBGA-84 (top view) . . . . .	8
Figure 2	Single-ended AC Input Test Conditions Diagram . . . . .	20
Figure 3	Differential DC and AC Input and Output Logic Levels Diagram . . . . .	20
Figure 4	AC Overshoot / Undershoot Diagram for Address and Control Pins . . . . .	23
Figure 5	AC Overshoot / Undershoot Diagram for Clock, Data, Strobe and Mask Pins . . . . .	24
Figure 6	Package Outline P(G)-TFBGA-84 . . . . .	33



# List of Tables

Table 1	Ordering Information for RoHS compliant products	3
Table 2	Chip Configuration of DDR2 SDRAM	5
Table 3	Abbreviations for Ball Type	7
Table 4	Abbreviations for Buffer Type	7
Table 5	DDR2 Addressing	9
Table 6	Mode Register Definition (BA[1:0] = 00 <sub>B</sub> )	10
Table 7	Extended Mode Register Definition (BA[1:0] = 01 <sub>B</sub> )	11
Table 8	EMRS(2) Programming Extended Mode Register Definition (BA[1:0]=10 <sub>B</sub> )	12
Table 9	EMR(3) Programming Extended Mode Register Definition( BA[1:0]=11 <sub>B</sub> )	13
Table 10	ODT Truth Table	14
Table 11	Burst Length and Sequence	14
Table 12	Command Truth Table	15
Table 13	Clock Enable (CKE) Truth Table for Synchronous Transitions	16
Table 14	Data Mask (DM) Truth Table	16
Table 15	Absolute Maximum Ratings	17
Table 16	DRAM Component Operating Temperature Range	17
Table 17	Recommended DC Operating Conditions (SSTL_18)	18
Table 18	ODT DC Electrical Characteristics	18
Table 19	Input and Output Leakage Currents	18
Table 20	DC & AC Logic Input Levels	19
Table 21	Single-ended AC Input Test Conditions	19
Table 22	Differential DC and AC Input and Output Logic Levels	20
Table 23	Full Strength Calibrated Pull-up Driver Characteristics	21
Table 24	Full Strength Calibrated Pull-down Driver Characteristics	21
Table 25	Input / Output Capacitance	22
Table 26	AC Overshoot / Undershoot Specification for Address and Control Pins	23
Table 27	AC Overshoot / Undershoot Specification for Clock, Data, Strobe and Mask Pins	24
Table 28	Speed Grade Definition	25
Table 29	Timing Parameter by Speed Grade	26
Table 30	ODT AC Characteristics and Operating Conditions for all bins	28
Table 31	I <sub>DD</sub> Measurement Conditions	29
Table 32	Definition for I <sub>DD</sub>	30
Table 33	I <sub>DD</sub> Specification	31
Table 34	I <sub>DD</sub> Measurement Test Condition	31
Table 35	ODT current per terminated input pin	32
Table 36	Package thermal characteristics	34



# Contents

<b>1</b>	<b>Overview</b> .....	<b>3</b>
1.1	Features .....	3
1.2	Description .....	4
<b>2</b>	<b>Configuration</b> .....	<b>5</b>
2.1	Chip Configuration .....	5
2.2	DDR2 Addressing .....	9
<b>3</b>	<b>Functional Description</b> .....	<b>10</b>
<b>4</b>	<b>Truth Tables</b> .....	<b>15</b>
<b>5</b>	<b>Electrical Characteristics</b> .....	<b>17</b>
5.1	Absolute Maximum Ratings .....	17
5.2	DC Characteristics .....	18
5.3	DC & AC Characteristics .....	19
5.4	Output Buffer Characteristics .....	21
5.5	Input / Output Capacitance .....	22
5.6	Overshoot and Undershoot Specification .....	23
5.7	AC Characteristics .....	25
5.7.1	Speed Grade Definitions .....	25
5.7.2	AC Timing Parameters .....	26
5.7.3	ODT AC Electrical Characteristics .....	28
<b>6</b>	<b>Currents Measurement Conditions</b> .....	<b>29</b>
6.1	I <sub>DD</sub> Test Conditions .....	31
6.1.1	On Die Termination (ODT) Current .....	32
<b>7</b>	<b>Package</b> .....	<b>33</b>
7.1	Package Dimension .....	33
7.2	Package Thermal Characteristics .....	34

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